(19) Europäisches Patentamt
European Patent Office
Office européen des brevets

(11) EP 2 731 136 A8

(12) CORRECTED EUROPEAN PATENT APPLICATION

(15) Correction information:
Corrected version no 1 (W1 A1)
Corrections, see
Bibliography INID code(s) 84

(48) Corrigendum issued on:
06.08.2014 Bulletin 2014/32

(43) Date of publication:
14.05.2014 Bulletin 2014/20

(21) Application number: **14154260.5**

(22) Date of filing: **22.01.2009**

(51) Int Cl.:
H01L 27/146 $^{(2006.01)}$

(84) Designated Contracting States:
DE FR NL

(30) Priority: **29.01.2008 JP 2008017743**
31.03.2008 JP 2008093858
15.08.2008 JP 2008209179

(62) Document number(s) of the earlier application(s) in accordance with Art. 76 EPC:
09000872.3 / 2 086 006

(71) Applicant: **Fujifilm Corporation**
Minato-ku
Tokyo (JP)

(72) Inventor: **Okada, Yoshihiro**
Kanagawa (JP)

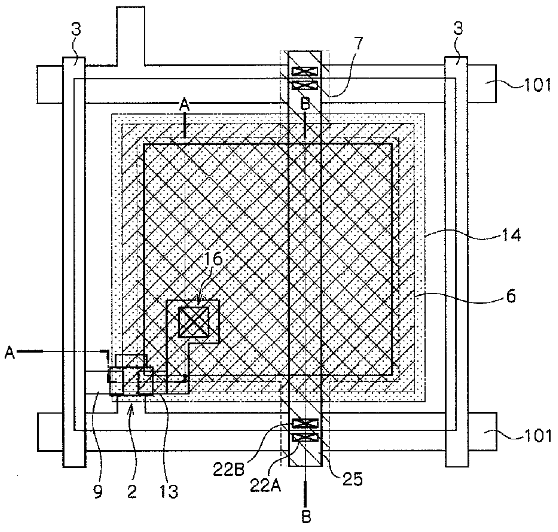
(74) Representative: **Klunker . Schmitt-Nilson . Hirsch**
Patentanwälte
Destouchesstraße 68
80796 München (DE)

Remarks:
This application was filed on 07-02-2014 as a divisional application to the application mentioned under INID code 62.

(54) Electromagnetic wave detecting element

(57) The present invention is to provide an electromagnetic wave detecting element that can prevent a decrease in light utilization efficiency at sensor portions. The sensor portions are provided so as to correspond to respective intersection portions of scan lines and signal lines, and have semiconductor layer that generate charges due to electromagnetic waves being irradiated, and at whose electromagnetic wave irradiation surface sides upper electrodes are formed, and at whose electromagnetic wave non-irradiation surface sides lower electrodes are formed. Bias voltage is supplied to the respective upper electrodes via respective contact holes by a common electrode line that is formed further toward an electromagnetic wave downstream side than the semiconductor layer.

FIG. 2



EP 2 731 136 A8

Printed by Jouve, 75001 PARIS (FR)